



ESCOLA POLITÉCNICA DA  
UNIVERSIDADE DE SÃO PAULO  
Departamento de Engenharia de Sistemas Eletrônicos PSI -  
EPUSP

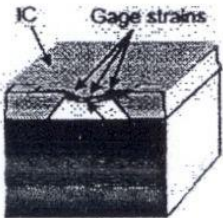
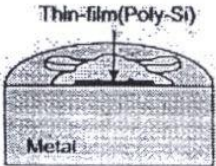
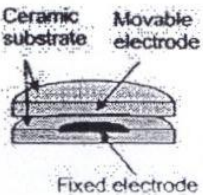
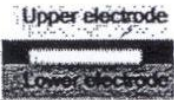
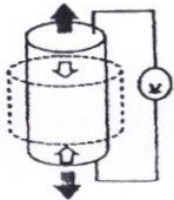


**PSI 2618**  
**CIRCUITOS ELETRÔNICOS AUTOMOTIVOS**

**Sensores de Pressão**

***Strain Gauge***

Tab. 7.3.1 Principles and features of pressure sensors

Principle	Piezoresistance		Capacitance		Piezoelectricity
	Silicon piezoresistance	Thin-film piezoresistance	Ceramic capacitance	Thin-film capacitance	Ceramic piezoelectricity
Structure					
Sensitivity	Middle $\Delta R = 1/2R\Delta\sigma\pi_{44}$ $\pi_{44}$ = Piezoresistive coefficient	Low $\pi_{44}$ = One sixth of single-crystal silicon	High	High	Low
Integration	Easy	Difficult	Difficult	Easy	Difficult
LSI process	Easy	Difficult	Difficult	Easy	Difficult

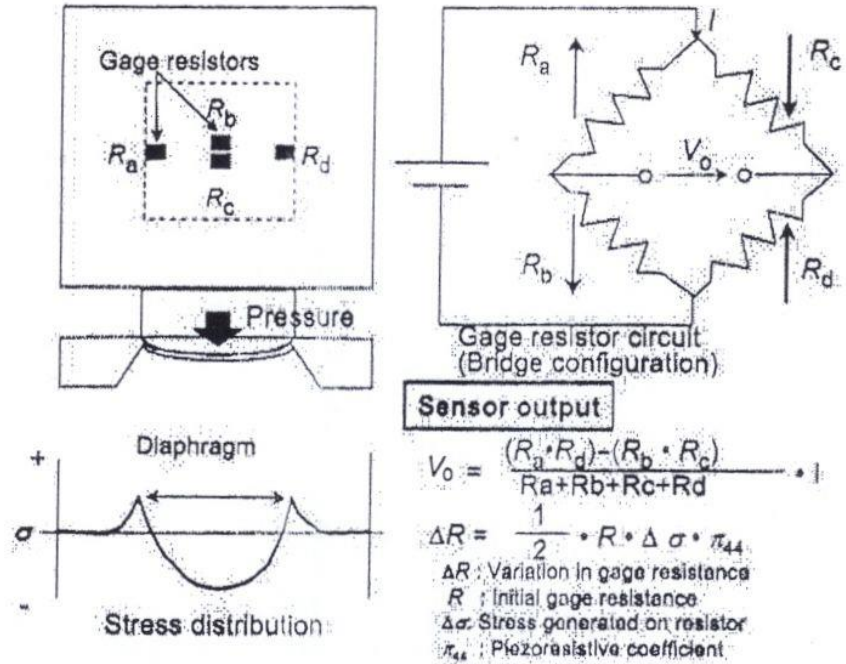


Fig. 7.3.1 Principle of piezoresistive sensor

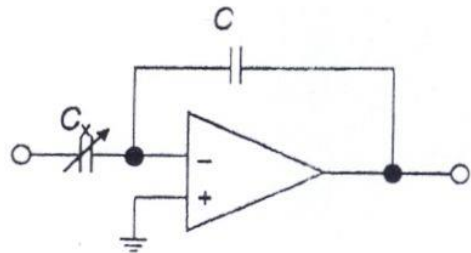





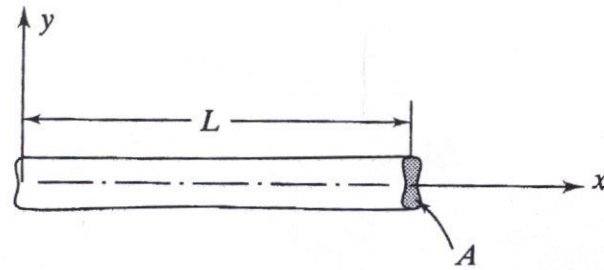


Fig. 7.3.2 Principle of capacitive sensor

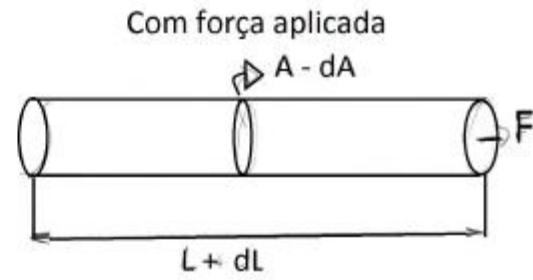
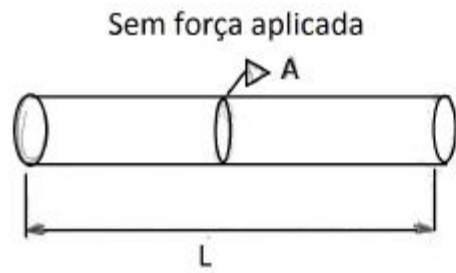
$$\Delta C \propto \frac{W^4}{\Delta t^3} \times \Delta P$$

	Low	Medium	High		
Pressure range	5 k Pa	100 k Pa	1~10 MPa	20 M Pa	200 M Pa
Product	Gasoline vapor	Intake pressure	Air-conditioning Suspension	Fuel pressure	Common
					

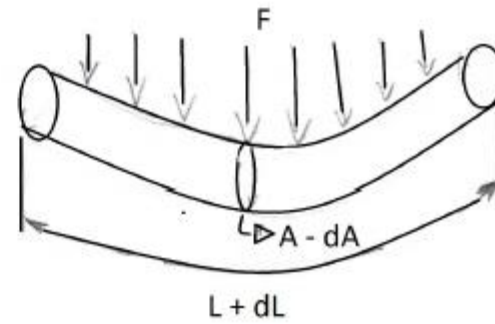
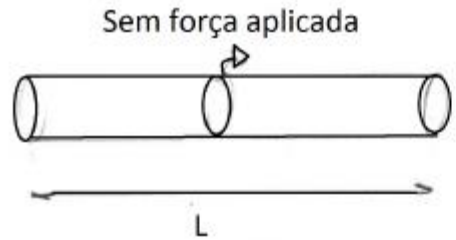


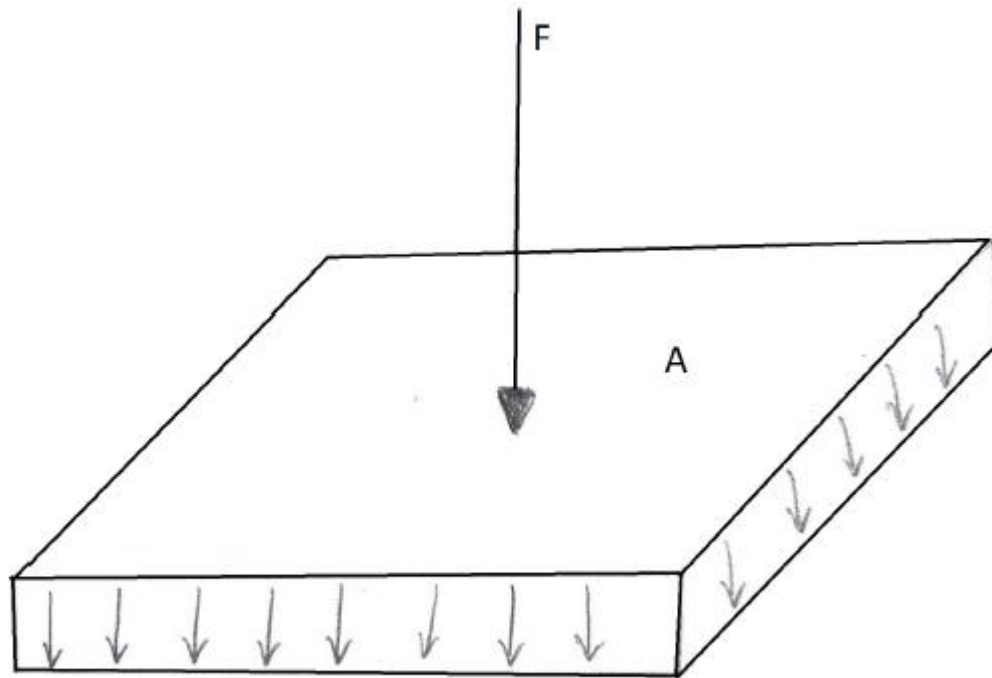
**FIGURE 5-2**  
A wire segment.

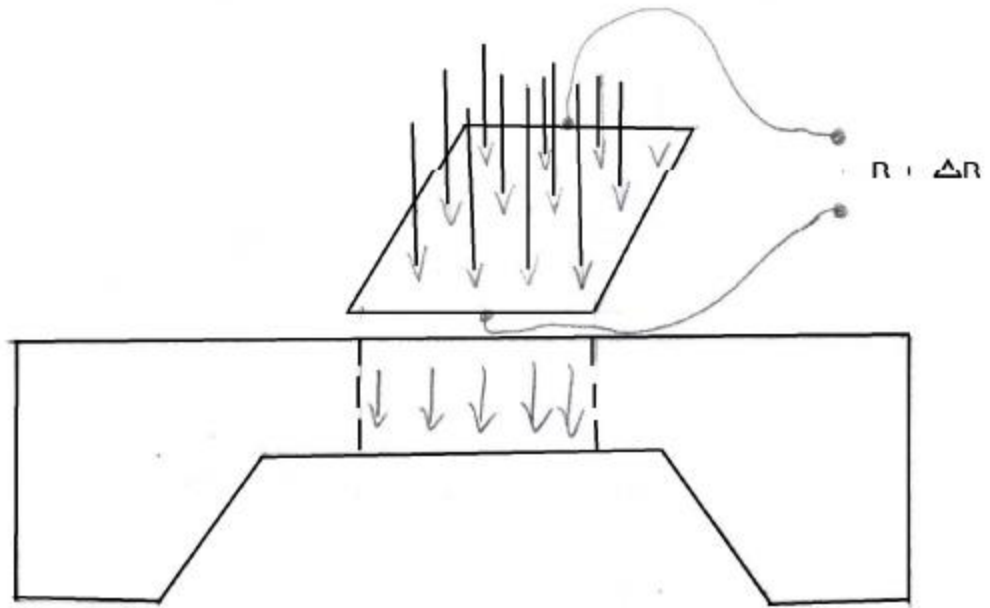
a)



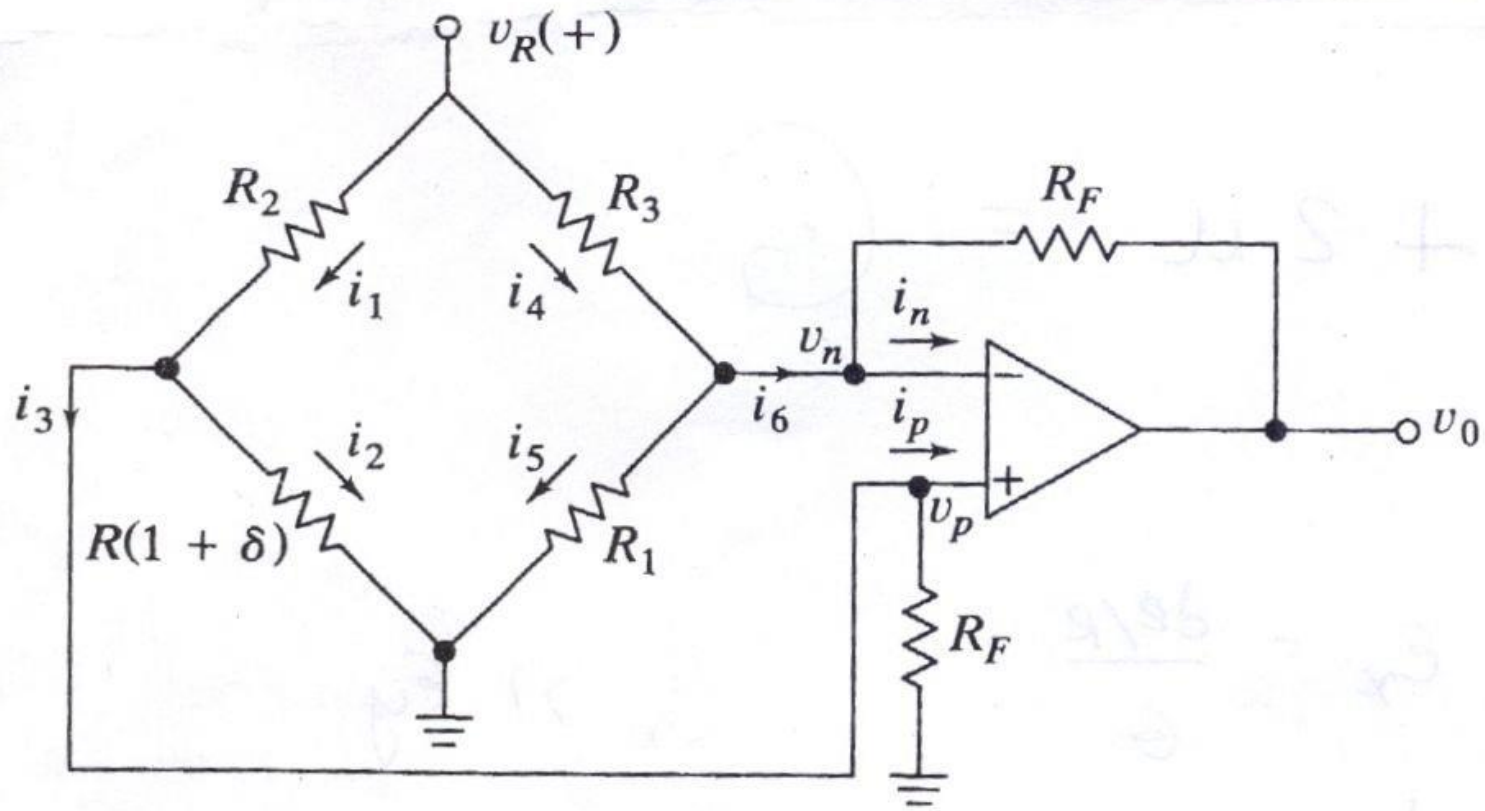
b)











**FIGURE 5-3**  
Strain gauge bridge circuit with differential amplifier.

$$i_1 = i_2 + i_3 \quad \text{and} \quad i_4 = i_5 + i_6$$

Use of Ohm's law across each device, together with  $i_n = 0$  and  $i_1 = i_2 + i_3$  finally yields the equations

$$\frac{v_R - v_p}{R_2} = \frac{v_p - 0}{R(1 + \delta)} + \frac{v_p - 0}{R_F}$$

$$\frac{v_R - v_n}{R_3} = \frac{v_n - 0}{R_1} + \frac{v_n - v_0}{R_F}$$

which result in

$$v_p = \frac{v_R}{R_2} \frac{R(1 + \delta)R_2R_F}{R_2R_2R_F + R(1 + \delta)(R_F + R_2)}$$

$$v_n = \left( \frac{v_R}{R_3} + \frac{v_0}{R_F} \right) \frac{R_1R_FR_3}{R_FR_3 + R_1R_3 + R_1R_F}$$

Substituting these two expressions yields  $v_0$  in the form

$$v_0 = \frac{v_R R_F}{R_1 R_3} \left[ \frac{R(1 + \delta)(R_F R_3 + R_1 R_3 - R_1 R_2) - R_1 R_2 R_F}{R_2 R_F + R(1 + \delta)(R_F + R_2)} \right]$$

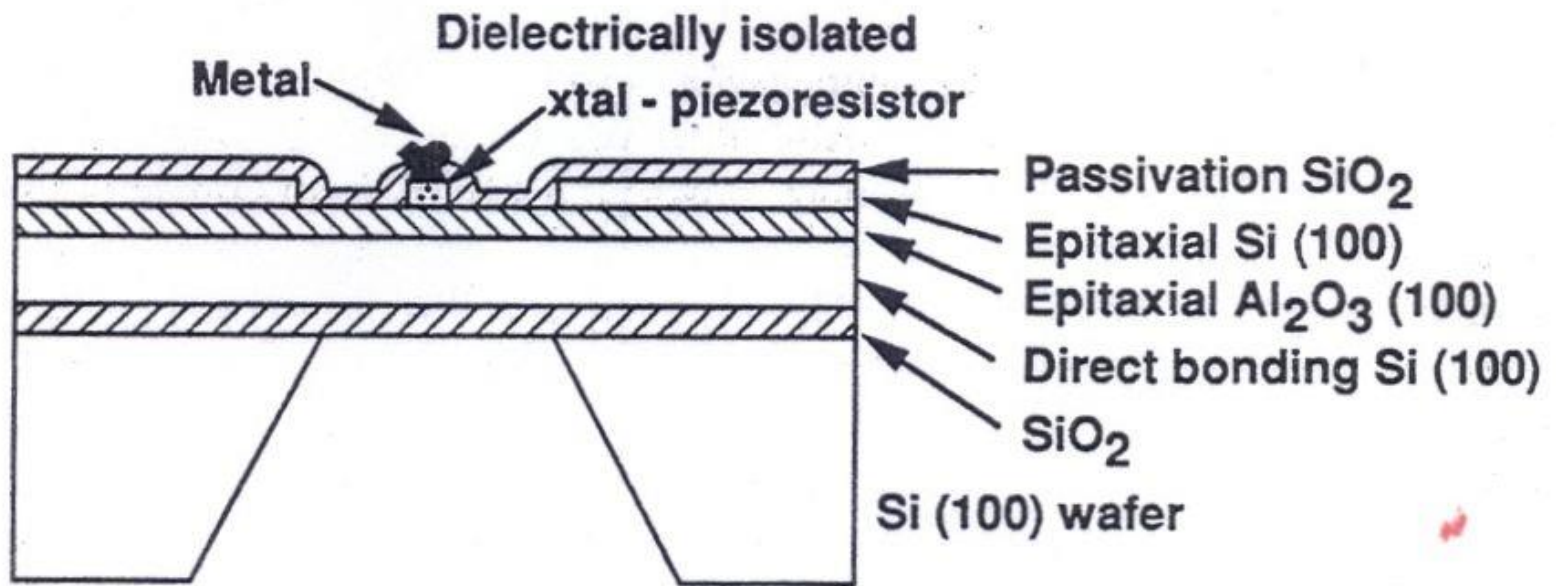
The expression simplifies considerably when two or more of the resistances are equal. Thus a choice of  $R_1 = R$  and  $R_2 = R_3 = R_0$  yields

$$v_0 = \frac{v_R R_F}{R} \left[ \frac{\delta}{\frac{R_0}{R} + (1 + \delta) \left( 1 + \frac{R_0}{R_F} \right)} \right]$$

If  $R_F \gg R_0$  and  $\delta \ll 1$ , the expression takes on the form

$$v_0 \approx \frac{v_R R_F}{R} \left[ \frac{\delta}{\frac{R_0}{R} + 1} \right]$$

(a)



(b)

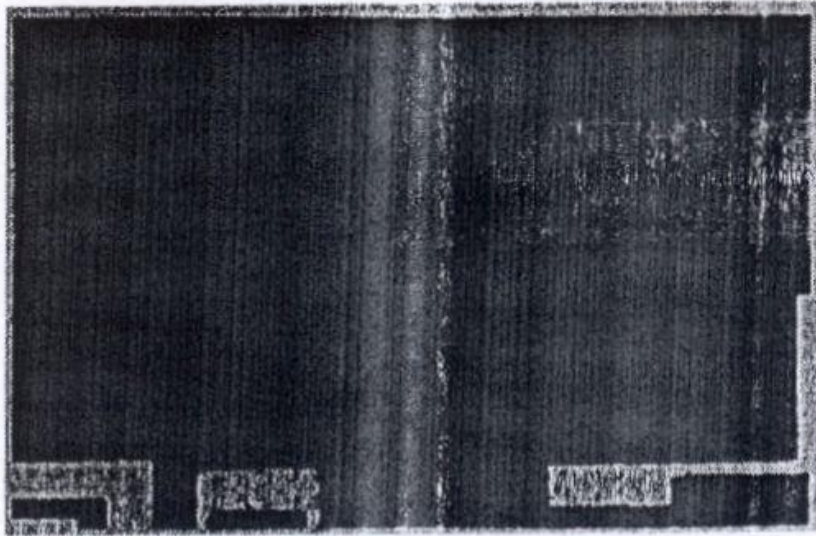


Fig. 7.3.6 Picture-frame photograph

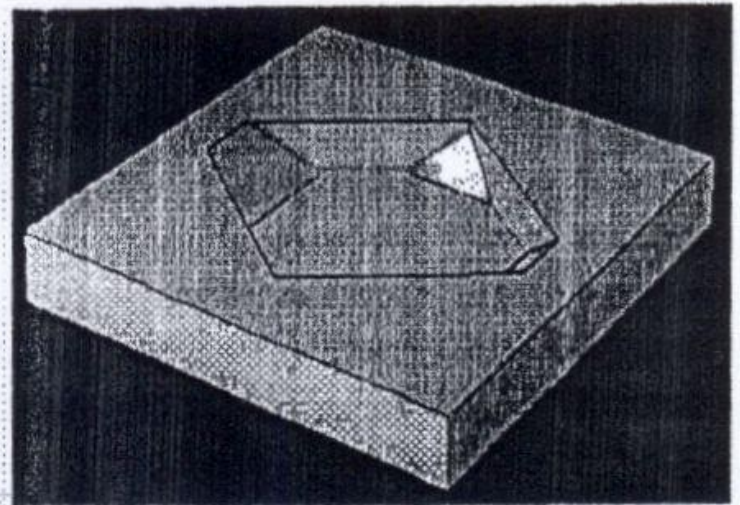
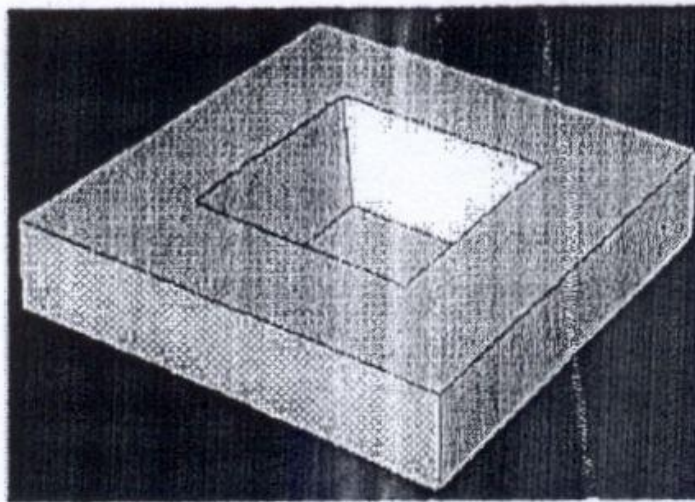
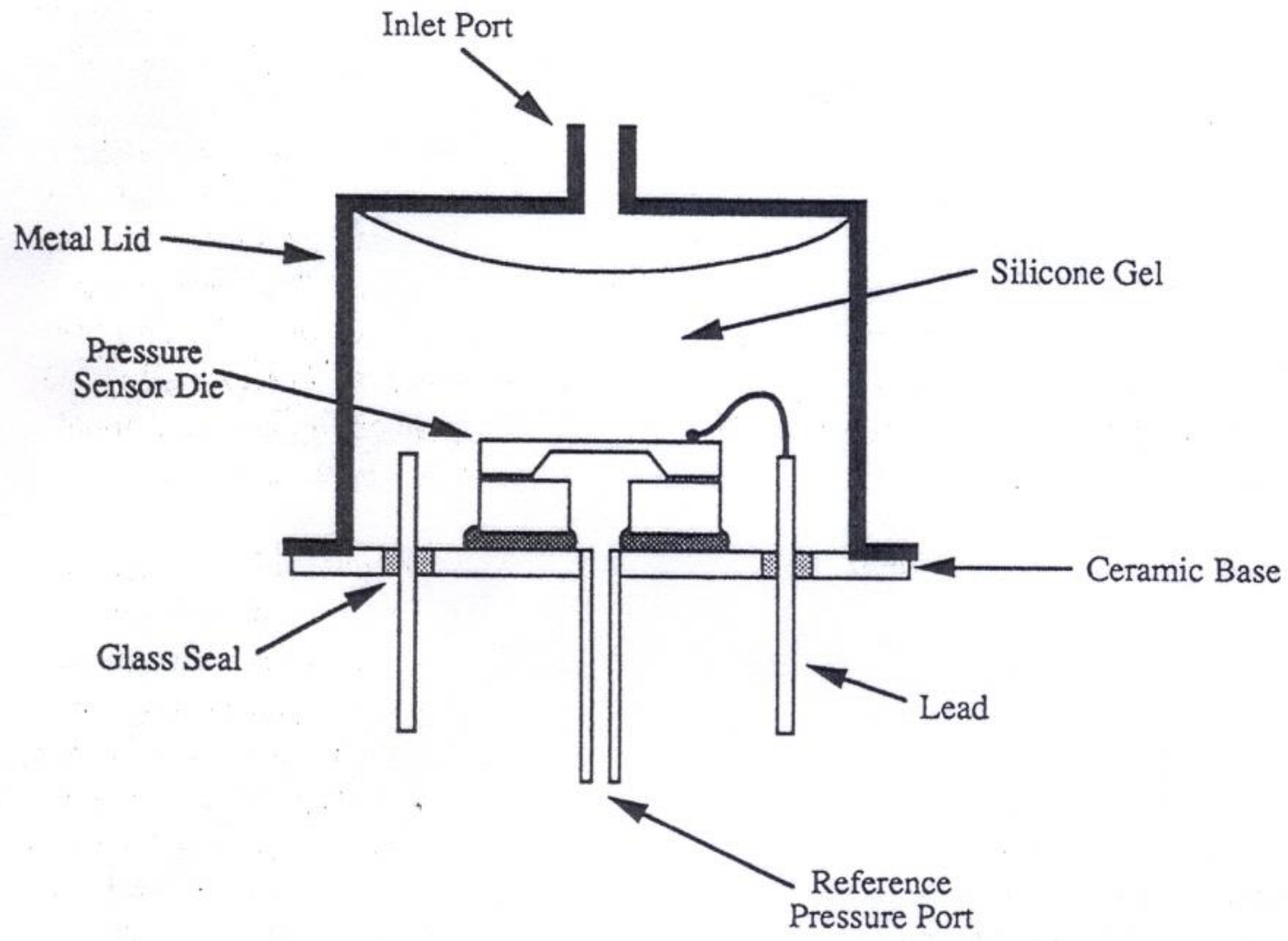
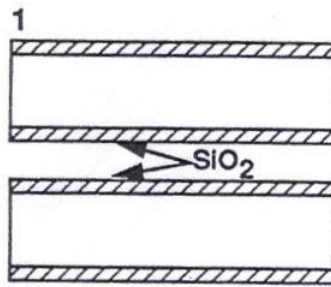


Fig. 7.3.7 Diaphragm geometries for silicon (100) and silicon (110)

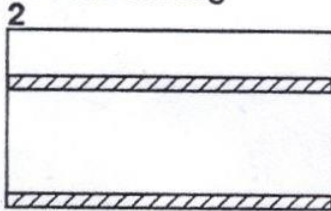


(b)

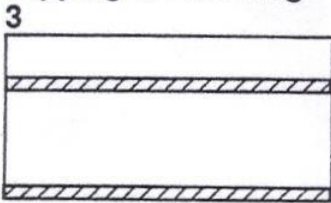




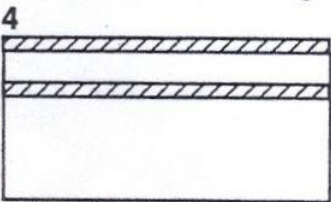
Direct Bonding



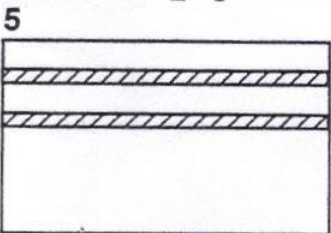
Lapping & Polishing



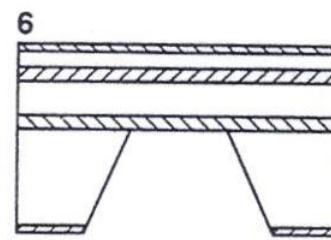
M - C Local Polishing



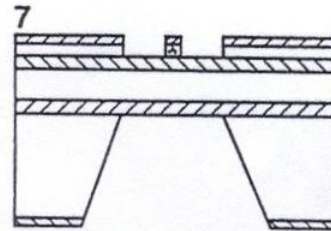
Epitaxial  $\text{Al}_2\text{O}_3$  Growth



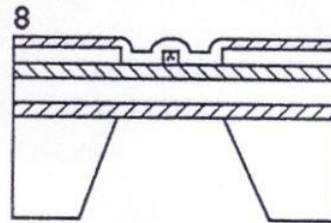
Epitaxial Si Growth



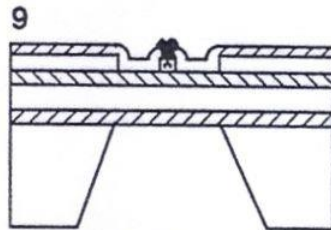
Diaphragm Formation



Piezoresistor  
Dielectric Isolation

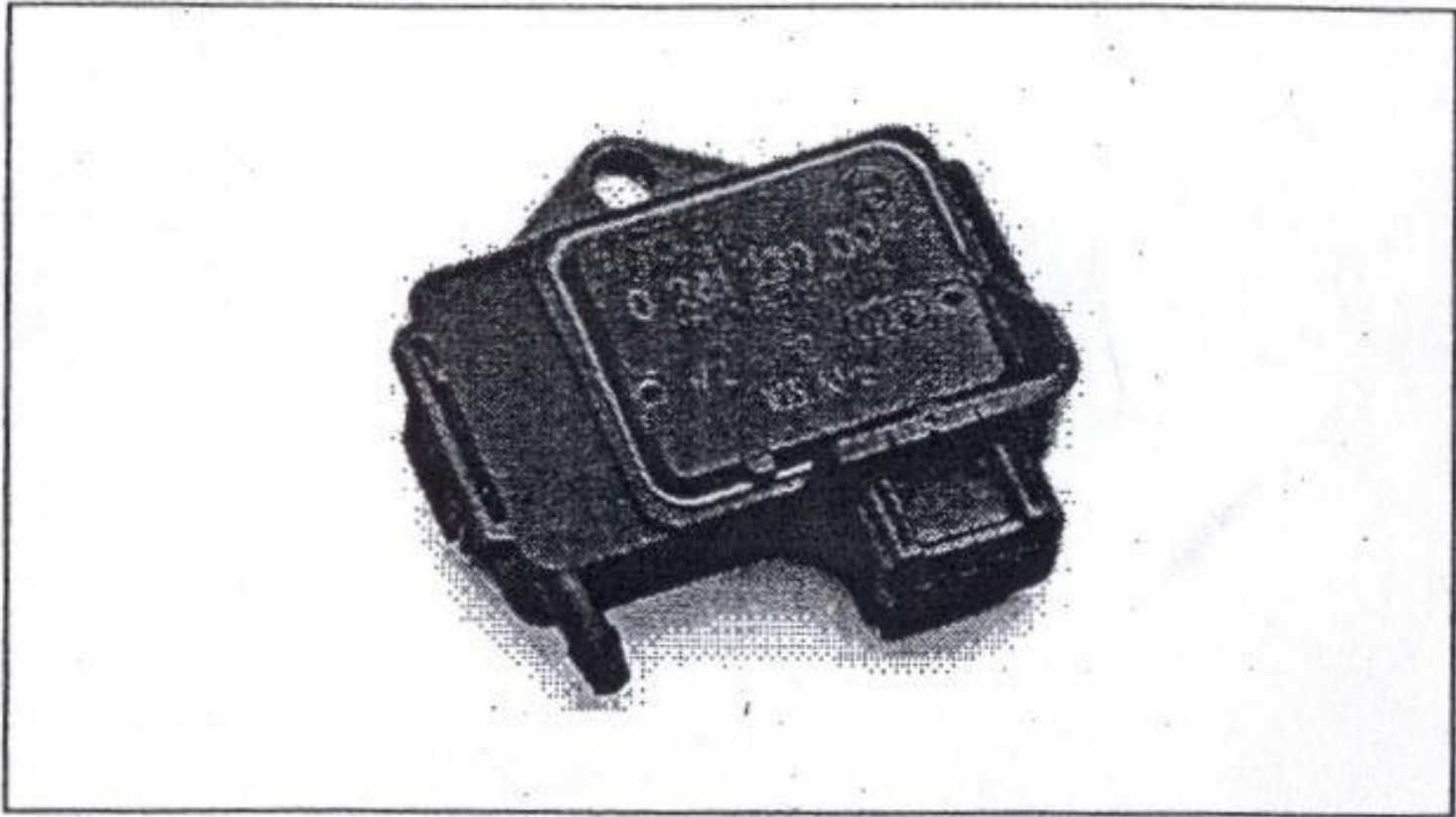


Passivation  $\text{SiO}_2$



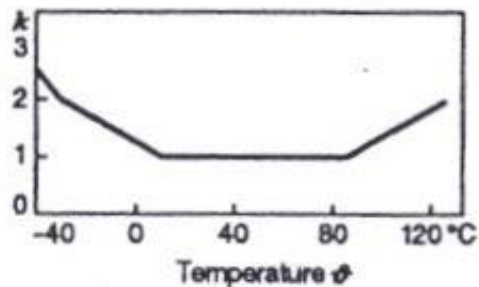
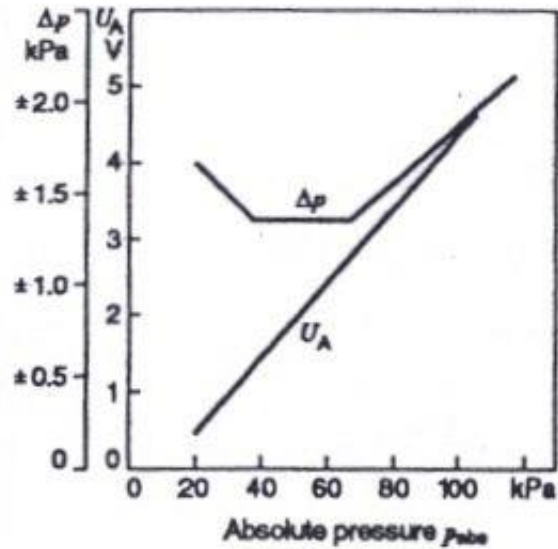
Electrode Formation

1



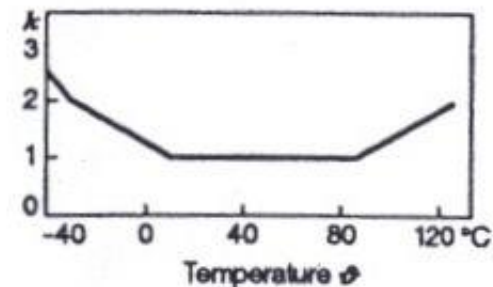
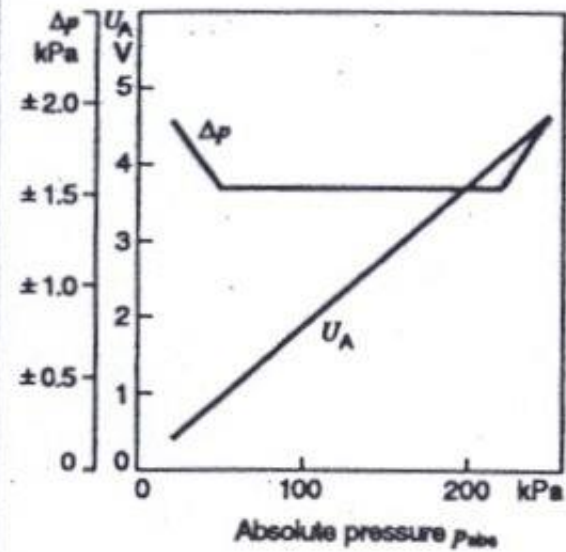
Characteristic curves 1 ( $U_V = 5 \text{ V}$ ).

$$U_A = U_V \cdot \left( 0,01 \frac{p_{abs}}{\text{kPa}} - 0,12 \right)$$



Characteristic curves 2 ( $U_V = 5 \text{ V}$ ).

$$U_A = U_V \cdot \left( \frac{0,85}{230} \cdot \frac{p_{abs}}{\text{kPa}} + 0,0061 \right)$$



Technical data / Range



Part number		0 261 230 004	0 281 002 119
Characteristic curve		1	2
Measuring range	kPa	20...105	20...250
Max. pressure (1 s, 30 °C)	kPa	600	500
Pressure-change time	ms	≤ 10	≤ 10
Supply voltage $U_V$	V	4.75...5.25	4.75...5.25
Max. supply voltage	V	16	16
Input current $I_Y$	mA	< 10	< 10
Load impedance $R_L$	kΩ	> 50	> 50
Operating temperature range	°C	-40...+125	-40...+120
Degree of protection		IP 54 A	-

## Accessories

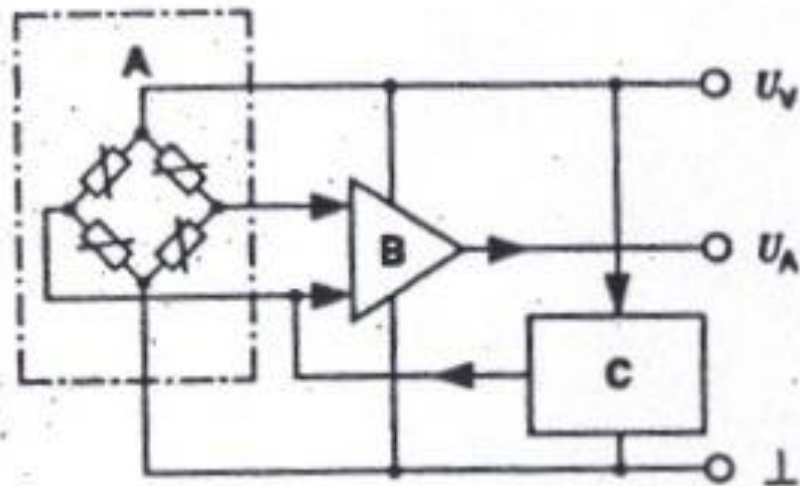
Connector	1 237 000 039
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**Block diagram.**

**A** Strain-gauge pressure-measuring cell,

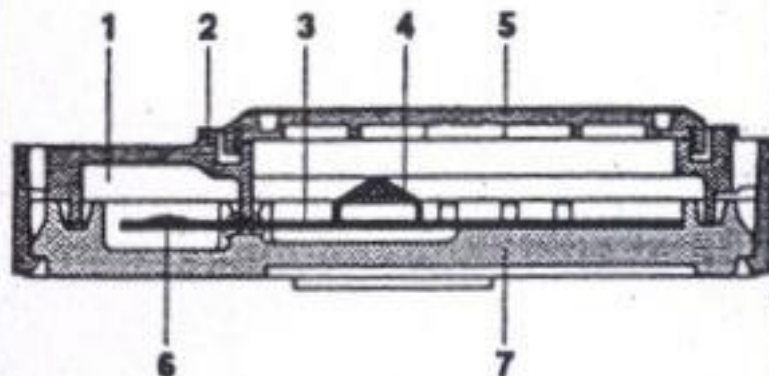
**B** Amplifier,

**C** Temperature-compensation circuit



### Design.

1 Strain-gauge pressure-measuring cell,  
2 Plastic housing, 3 Thick-film hybrid  
(sensor and evaluation circuit), 4 Operational  
amplifier, 5 Housing cover, 6 Thick-film sensor  
element (sensor bubble), 7 Aluminum base  
plate.



### Installation instructions

A hose forms the connection between the sensor and the gas pressure to be measured. Upon installation, the sensor pressure connection should point downwards to prevent the ingress of moisture.

The angular position referred to the vertical must be  $+20^{\circ}$ ... $-85^{\circ}$ , preferably  $0^{\circ}$ .

Suggested fastening:

M6 screw with spring washer.

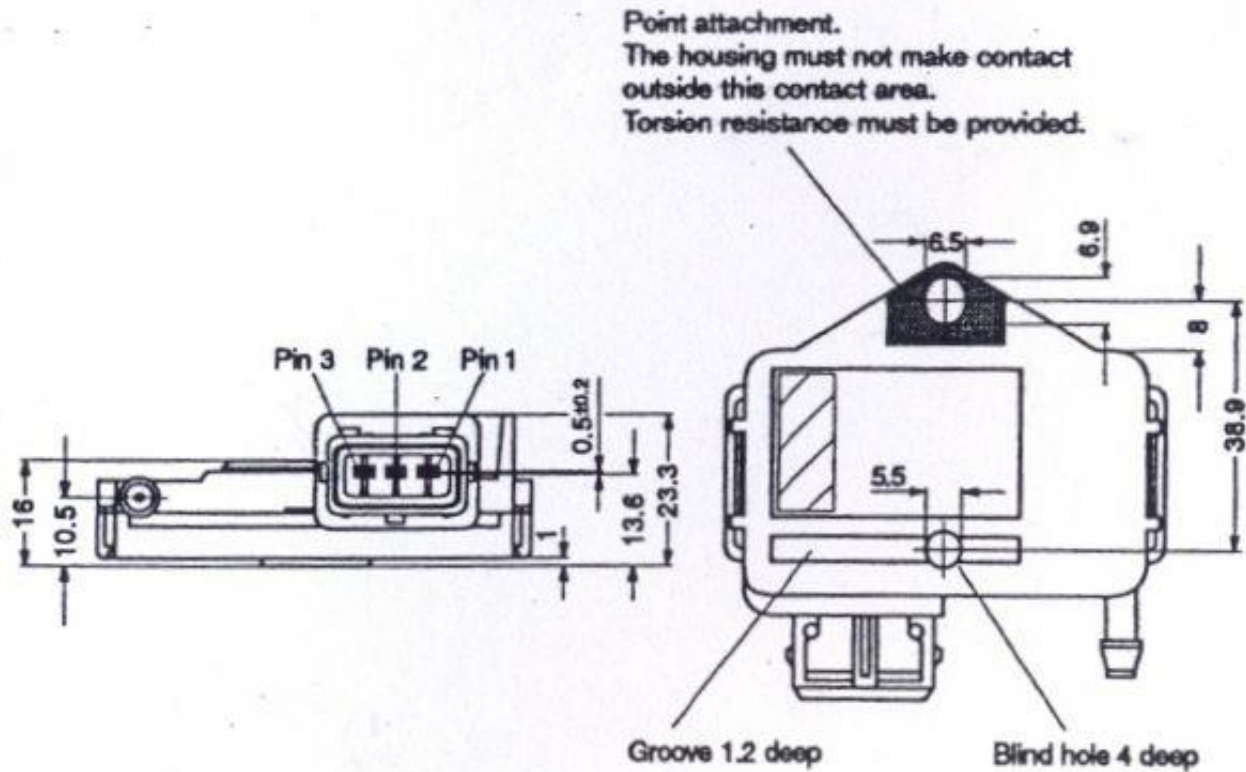
### Connector-pin assignment

Terminal 1  $+U_V$

Terminal 2 Ground

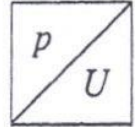
Terminal 3  $U_A$

Dimension drawings.

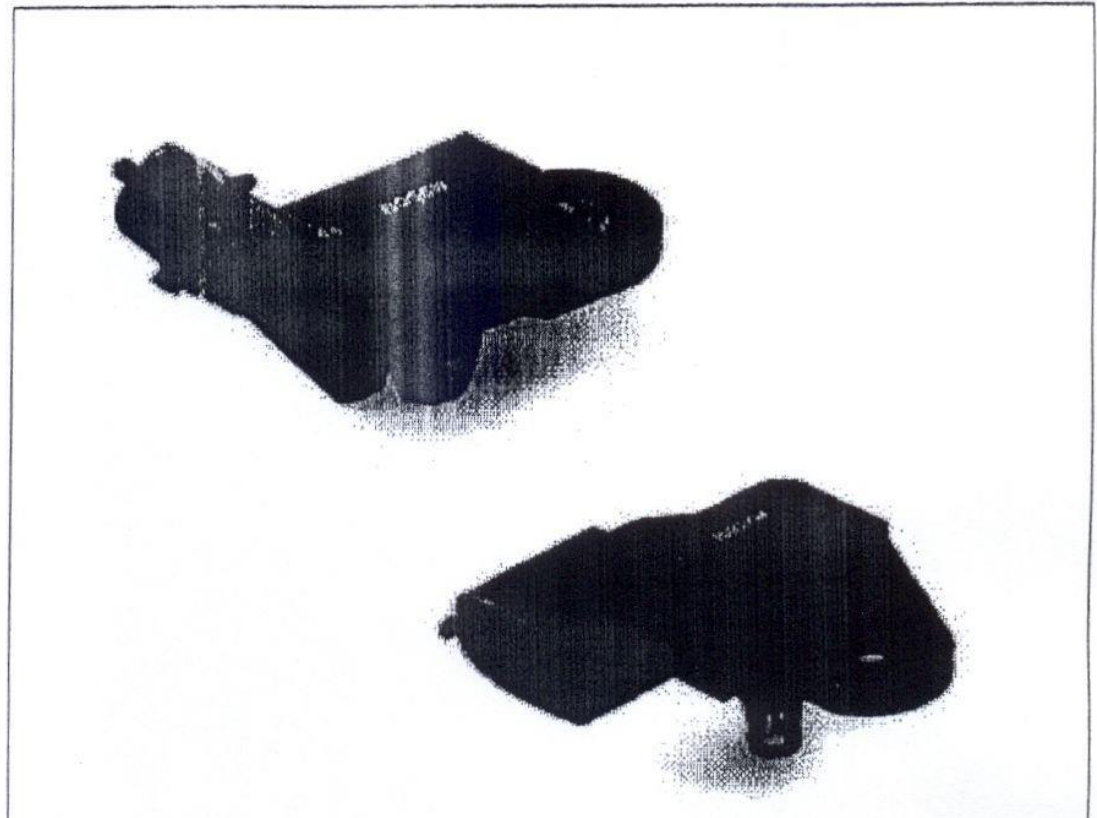


# Absolute-pressure sensors in micromechanical hybrid design

Measurement of pressures in gases up to 400 kPa



- High accuracy.
- EMC protection better than  $100 \text{ V m}^{-1}$ .
- Temperature-compensated.
- Version with additional integral temperature sensor.





Pressure range kPa (p <sub>1</sub> ...p <sub>2</sub> )	Characteristic curve <sup>1)</sup>	Features	Dimension drawing <sup>2)</sup>	Order No.
10...115	1		1	<b>B 261 260 136<sup>3)</sup></b>
10...115	1		2	<b>0 261 230 052</b>
20...250	1		1	<b>0 281 002 487</b>
10...115	1	Integral temperature sensor	3	<b>0 261 230 030</b>
20...250	1	Integral temperature sensor	3	<b>0 261 230 042</b>
20...300	1	Integral temperature sensor	3	<b>0 281 002 437</b>
50...350	2	Integral temperature sensor	3	<b>0 281 002 456</b>
50...400	2	Integral temperature sensor	3	<b>B 261 260 508<sup>3)</sup></b>

<sup>1)</sup> The characteristic-curve tolerance and the tolerance expansion factor apply for all versions, see Page 36

<sup>2)</sup> See Page 37

<sup>3)</sup> Provisional draft number, order number available upon enquiry. Available as from about the end of 2001

## Technical data

			min.	typ.	max.
Operating temperature	$\vartheta_B$	$^{\circ}\text{C}$	-40	-	+130
Supply voltage	$U_V$	V	4.5	5.0	5.5
Current consumption at $U_V = 5\text{ V}$	$I_V$	mA	6.0	9.0	12.5
Load current at output	$I_L$	mA	-1.0	-	0.5
Load resistance to $U_V$ or ground	$R_{\text{pull-up}}$	$\text{k}\Omega$	5	680	-
	$R_{\text{pull-down}}$	$\text{k}\Omega$	10.0	100	-
Response time	$t_{10/90}$	ms	-	1.0	-
Voltage limitation at $U_V = 5\text{ V}$					
Lower limit	$U_{A\text{ min}}$	V	0.25	0.3	0.35
Upper limit	$U_{A\text{ max}}$	V	4.75	4.8	4.85

### Limit data

Supply voltage	$U_{V\text{ max}}$	V	-	-	+16
Storage temperature	$\vartheta_L$	$^{\circ}\text{C}$	-40	-	+130

### Temperature sensor

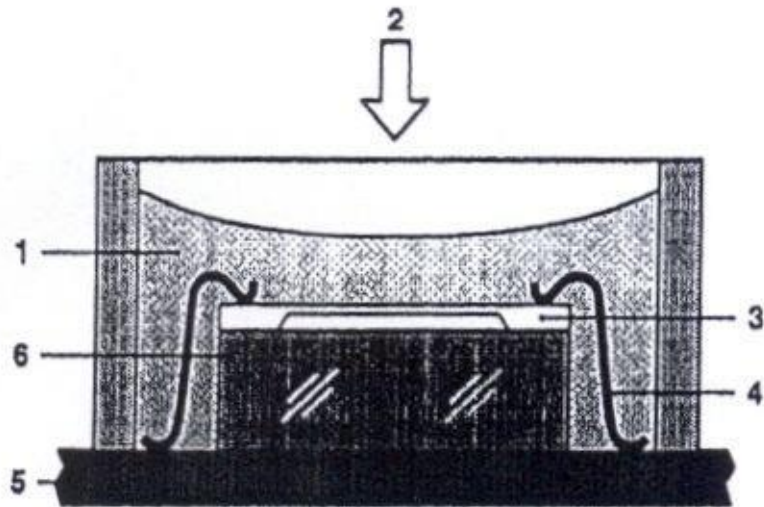
Measuring range	$\vartheta_M$	$^{\circ}\text{C}$	-40	-	+130
Measured current	$I_M$	mA	-	-	1 <sup>1)</sup>
Nominal resistance at +20 $^{\circ}\text{C}$		$\text{k}\Omega$	-	$2.5 \pm 5\%$	-
Thermal time constant	$t_{63}$	s	-	-	$10^2$ )

1) Operation at 5 V with 1  $\text{k}\Omega$  series resistor

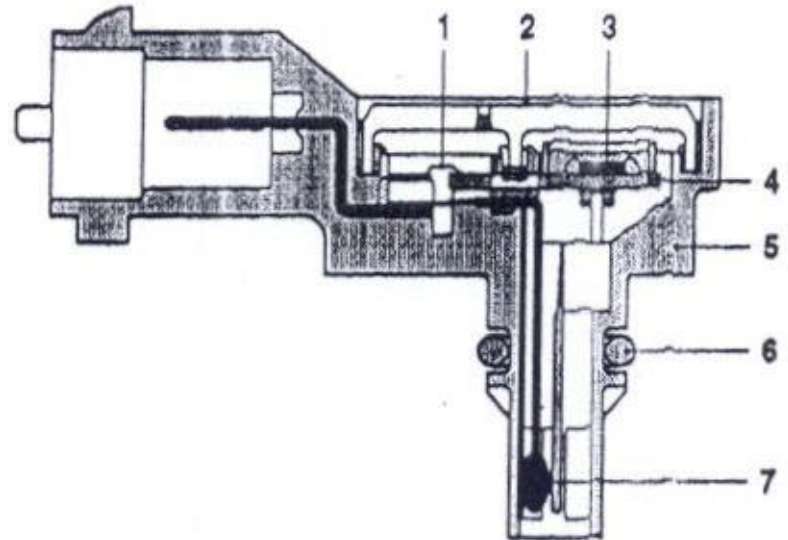
2) In air with a flow rate of  $6\text{ m} \cdot \text{s}^{-1}$

Sectional view.

Section through the sensor cell



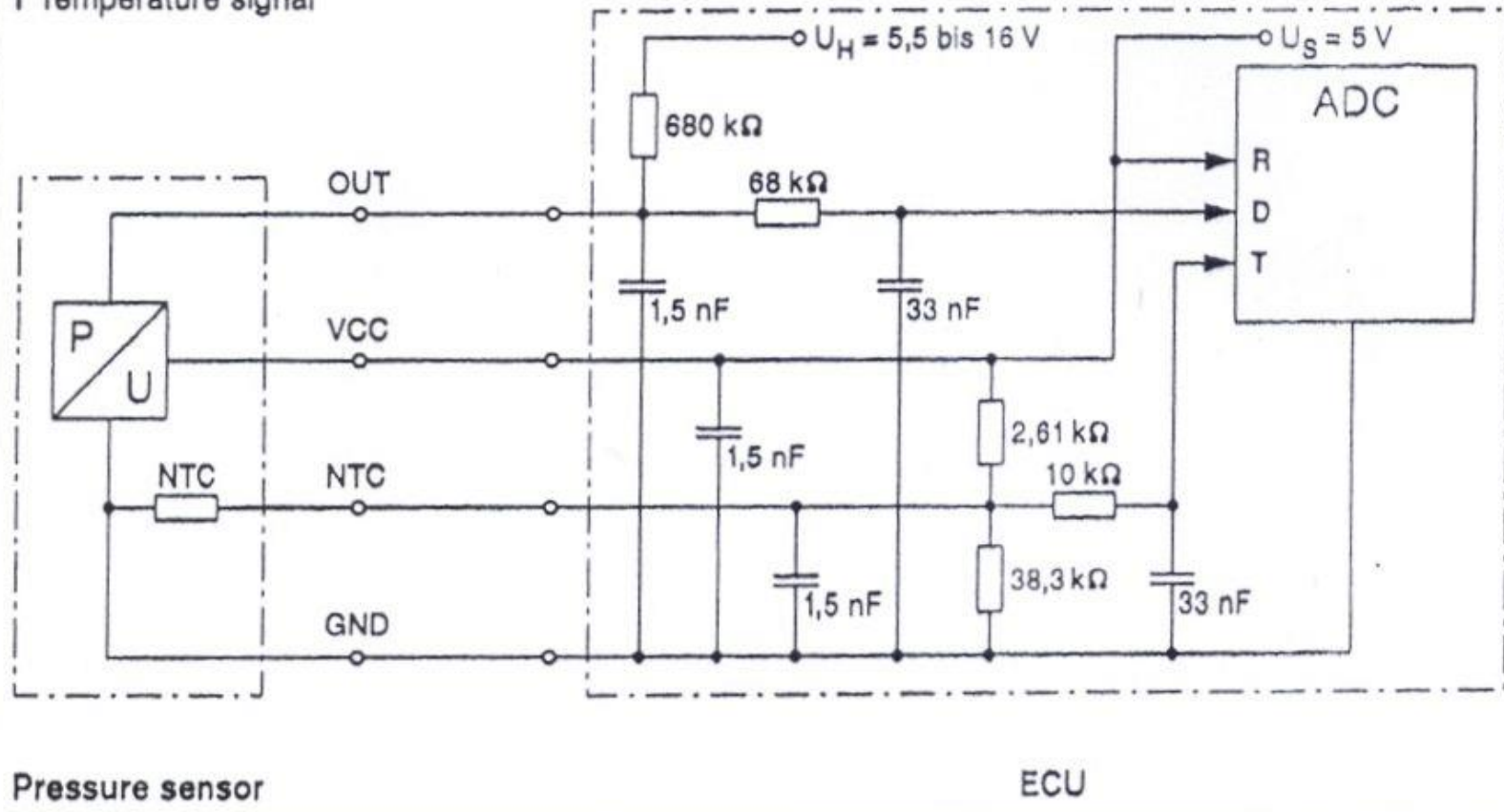
Section through the DS-S2 pressure sensor



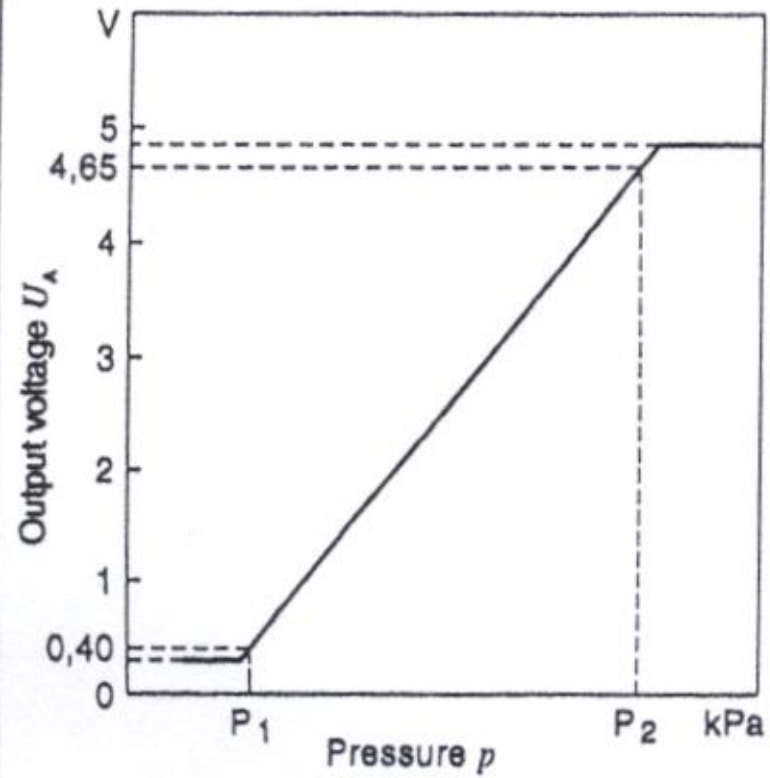


Signal evaluation: Recommendation.

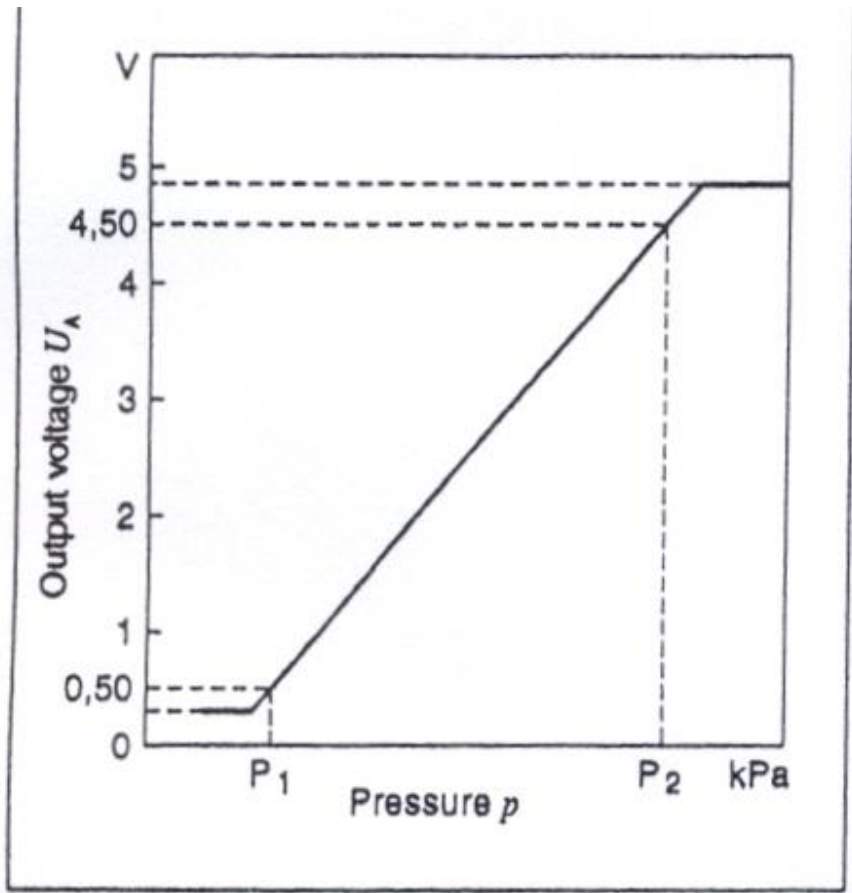
- R Reference
- D Pressure signal
- T Temperature signal



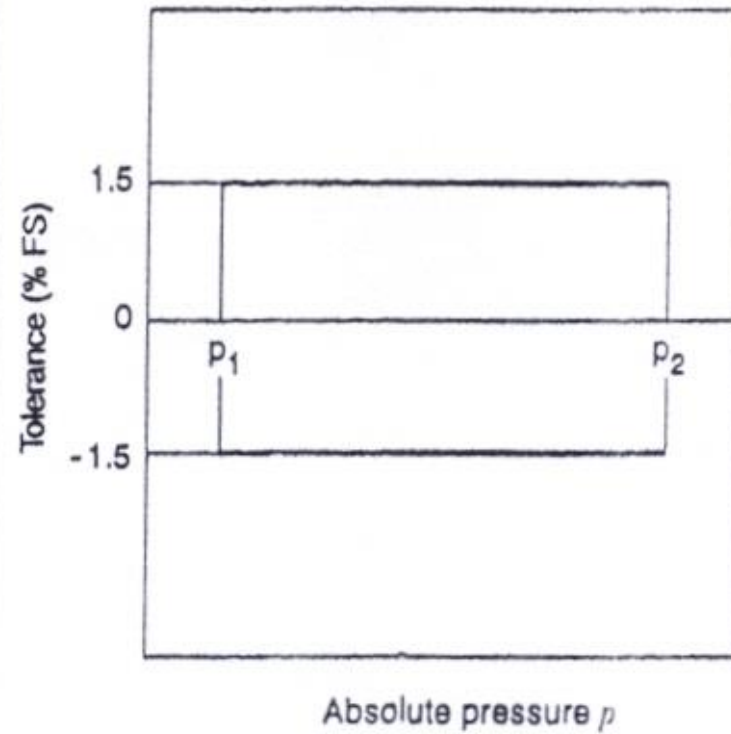
Characteristic curve 1 ( $U_V = 5.0 \text{ V}$ ).



Characteristic curve ( $U_V = 5.0 \text{ V}$ ).

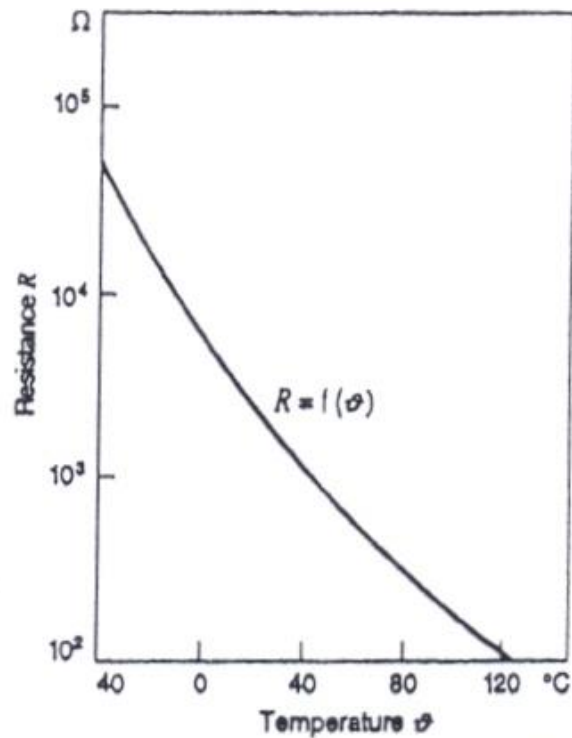


**Characteristic-curve tolerance.**



**Tolerance-expansion factor.**

Temperature-sensor characteristic curve.



**Explanation of symbols.**

$U_A$  Output voltage

$U_V$  Supply voltage

$k$  Tolerance multiplier

D After continuous operation

N As-new state